PNP Epitaxial Silicon Transistor

KSA916

Features

- Audio Power Amplifier
- Driver Stage Amplifier
- Complement to KSC2316

ABSOLUTE MAXIMUM RATINGS

(Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-120	V
V _{CEO}	Collector-Emitter Voltage	-120	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-800	mA
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

(Values are at T_A = 25°C unless otherwise noted.) (Note 1)

Symbol	Parameter	Value	Unit	
P _D	Power Dissipation, by $R_{\theta JA}$	900	mW	
	Power Dissipation, by $R_{\theta JC}$	3	W	
	Derate Above 25°C, by R _{θJA}	7.2	mW/°C	
	Derate Above 25°C, by R _{θJC}	24	mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	130	°C/W	
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case	41	°C/W	

^{1.} PCB size: FR-4, 76 mm \times 114 mm \times 1.57 mm (3.0 inch \times 4.5 inch \times 0.062 inch) with minimum land pattern size.



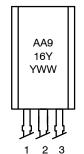
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TO-92 3 LF CASE 135AM

MARKING DIAGRAM



- 1: Emitter
- 2: Collector
- 3: Base

A = Assembly Code A916Y = Device Code YWW = Date Code

ORDERING INFORMATION

Device	Package	Shipping
KSA916YTA	TO-92 3 LF (Pb-Free)	2000 / Fan–Fold

KSA916

ELECTRICAL CHARACTERISTICS

(Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = -1 \text{ mA}, I_E = 0$	-120	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -10 \text{ mA}, I_B = 0$	-120	-	-	V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = -1 \text{ mA}, I_C = 0$	-5	ı	-	V
I _{CBO}	Collector Cut-Off Current	$V_{CB} = -120 \text{ V}, I_{E} = 0$	-	-	-0.1	μΑ
h _{FE1}	DC Current Gain	$V_{CE} = -5 \text{ V}, I_{C} = -10 \text{ mA}$	60	ı	ı	
h _{FE2}	DC Current Gain	$V_{CE} = -5 \text{ V}, I_{C} = -100 \text{ mA}$	80	-	240	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$	-	-	-1	V
f _T	Current Gain Bandwidth Product	$V_{CE} = -5 \text{ V}, I_{C} = -100 \text{ mA}$	-	120	-	MHz
C _{ob}	Output Capacitance	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	-	-	40	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

$h_{\mbox{\scriptsize FE}}$ CLASSIFICATION

Classification	0	Y
h _{FE2}	80 ~ 160	120 ~ 240

KSA916

TYPICAL PERFORMANCE CHARACTERISTICS

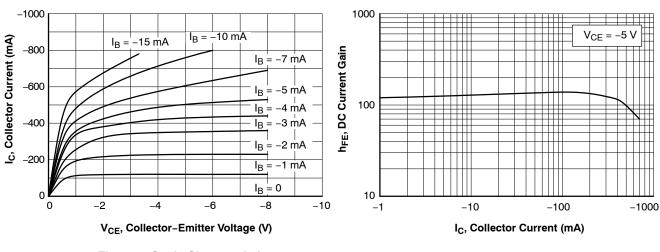
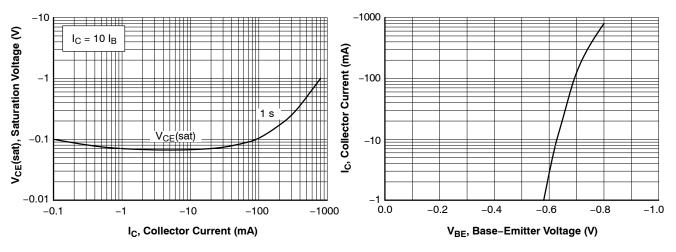


Figure 1. Static Characteristic

Figure 2. DC Current Gain



Single Pulse

10 ms

1 ms

-100

Figure 3. Collector-Emitter Saturation Voltage

DC Operating $T_C = 25^{\circ}C$

100 ms

I_C, Collector Current (A)

-10

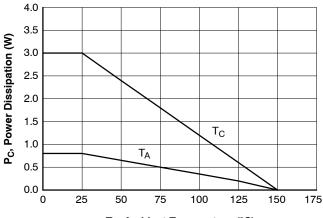


Figure 4. Base-Emitter On Voltage

V_{CE}, Collector-Emitter Voltage (V) Figure 5. Safe Operating Area

-10

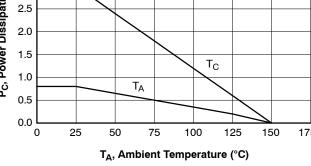
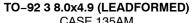


Figure 6. Power Derating



CASE 135AM ISSUE B

DATE 14 JAN 2021



- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, GATE REMAINS AND TIE BAR PROTRUSIONS.
- 4. DIMENSION & AND &2 DOES NOT INCLUDE DAMBAR PROTRUSION.
 DIMENSION &2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	3.70	3.90	4.10	
A1	1.25	1.45	1.65	
b	0.35	0.50	0.60	
b2	0.62		0.78	
С	0.35	0.45	0.55	
D	7.80	8.00	8.20	
Ε	4.70	4.90	5.10	
E2	3.70	3.90	4.10	
е	1.27 BSC			
e2	2.50 BSC			
F	2.45 REF			
L	13.00 REF			
L2	1.50		1.90	
L3	2.60		3,40	
L4	10.40 REF			

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END VIEW

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